

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)	Application Number	10727746
	Filing Date	2003-12-03
	First Named Inventor	Heng Liu
	Art Unit	1792
	Examiner Name	Ram N. Kackar
	Attorney Docket Number	M-15626-1D US

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	1	J. DAI "Atmospheric pressure MOCVD Growth of high-quality ZnO films on A1 O templates", Journal of Crystal Growth 283 (2005), pp. 93-99	<input type="checkbox"/>
	2	Theodoropoulos et al. "Design of gas inlets for the growth of gallium nitride by metalorganic vapor phase epitaxy", Journal of Crystal Growth 217 (200), pp. 65-81	<input type="checkbox"/>
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